科目コード(Code)	科目名 (Course title)	Course title (English)
10C710	電子工学特別実験及演習1	Advanced Experiments and Exercisesin Electronic Science and Engineering I
10C713	電子工学特別実験及演習2	Advanced Experiments and Exercisesin Electronic Science and Engineering II
10C825	量子論電子工学	Quantum Theory for Electronics
10C800	半導体ナノスピントロニクス	Semiconductor Nanospintronics
10C801	電子装置特論	Charged Particle Beam Apparatus
10C803	量子情報科学	Quantum Information Science
10C810	半導体工学特論	Semiconductor Engineering, Adv.
10C813	電子材料学特論	Electronic Materials, Adv.
10C816	分子エレクトロニクス	Molecular Electronics
10C819	表面電子物性工学	Surface Electronic Properties
10C822	光物性工学	Optical Properties and Engineering
10C828	光量子デバイス工学	Quantum Optoelectronics Devices
10C830	量子計測工学	Quantum measurement
10C851	電気伝導	Electrical Conduction in Condensed Matter
693631	集積回路工学特論	Integrated Circuits Engineering, Adv.
10X001	融合光・電子科学の展望	Prospects of Interdisciplinary Photonics and Electronics
10C846	電子工学特別研修1(インターン)	Advanced Seminar in Electronic Science and Engineering I
10C848	電子工学特別研修2(インターン)	Advanced Seminar in Electronic Science and Engineering II

											未更新		
Numbering code													
Course title <english></english>		エ学特別実! ed Experiments and Exer			Engineering I	dep	liated artment title,Na	,			ol of Engineering OTO TSUNENOBU		
Target ye	ar			Number	of cred	lits	4			e offered eriod	2019/Intensive, year-round		
Day/perio		ntensive		ss style	Experin	ment				Language	Japanese		
[Outline a	nd P	Purpose of t	he C	ourse]									
[Course Goals]													
[Course S	[Course Schedule and Contents]												
,30times,				_									
[Class rec	quire	ment]											
None													
[Method, I	Poin	t of view, ar	nd At	tainment	levels	of E	valuat	ion]				
• ·								-	•				
[Textbook	k]												
	_												
[Referenc	e bo	oks, etc.]											
- (Referei		_											
[Regardin	g st	udies out of	clas	s (prepara	ation a	nd r	eview)]					
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(Others (offic	e hour, etc.))										
-		LASIS to find	-	about office	hours.								

											未更新	
Numbering code												
Course title <english></english>		エ学特別実! ed Experiments and Exerc			Engineering II	depa	iated artment title,Na	,			ol of Engineering OTO TSUNENOBU	
Target ye	ar			Number	of cred	lits 4	1			e offered eriod	2019/Intensive, year-round	
Day/perio		ntensive		ss style	Experin	ment				Language	Japanese	
[Outline a	nd P	Purpose of t	he C	ourse]								
[Course Goals]												
[Course Schedule and Contents]												
- ,30times,				-								
[Class red	luire	ment]										
None												
[Method.]	Poin	t of view, ar	nd Af	tainment	levels	of Ev	/aluat	ion	1			
L	•••••											
[Textbook	k]											
[Referenc	e bo	oks, etc.]										
(Referei	nce l	oooks)										
[Regardin	g st	udies out of	clas	s (prepara	ation a	nd re	eview)]				
	_											
(Others (offic	e hour, etc.))									
*Please visit	t KU	LASIS to find	louta	about office	hours.							

Numbering	g code													
Course title <english></english>		電子工学 m Theory		lectronics		dep	iliated partment p title,Na				ol of Engineering sor,KAKEYA ITSUHIRO			
Target ye	ar			Number	of cred	lits	2			e offered eriod	2019/First semester			
Day/perio	d Tue.	3	Cla	ss style	Lecture	e				Language	Japanese			
[Outline a	nd Pur	pose of t	he C	ourse]										
Based on the fundamental understanding of quantum mechanics, we start with hydrogen atom of 1 atom and 1 hydrogen atom, hydrogen molecule ion of 2 atom electrons, hydrogen molecule of 2 atom 2 electrons, 1 electron Lecture on how to calculate the electronic state when increasing the number from the next step. We will also talk about molecular models consisting of a plurality of atoms. In order to understand fundamental handling in the case of multi electron system, consider Coulomb interaction, spin orbit interaction, as an interaction received by electrons. Simultaneously, we give an approximate calculation method necessary for these calculations.														
[Course G	[Course Goals]													
Based on the fundamental understanding of quantum mechanics, we acquire knowledge and thinking to the extent that approximate calculation can be performed on a simple problem. In addition, we will acquire academic ability to read only specialized books such as solid state electronics based on quantum theory.														
[Course S	chedul	e and Co	onten	its]										
Review and Review the							nd repai	r nc	otatio	on method to	o learn from now.			
	method m while	, perturbat solving ex	tion n tercis	es. The app	roximati	on r	nethod				on method, variational es the basis of the			
Combined w We describe	-				for unde	ersta	nding th	ne el	lectr	onic level a	nd its composition.			
multiple elec	ng the spectron ato tions and	pin orbit in oms and th d explain o	e elec quanti	tronic level	in solid	ls. H	lere, I w	ill g	give	lectures and	e electronic level of descriptions of spin erturbation method and			
I will give a of microstru magnitude a	Multiplet (1 time) I will give a lecture on the electronic level of multiple electron atoms. In particular, we will clarify the origin of microstructure and understand how electron level is split by Coulomb interaction, spin orbit interaction, its magnitude and number of divisions. In addition, we describe empirical Hunt 's law concerning the ground state of such multi - electron atoms.													
Zeeman effe	ct (2 tin	nes)												
								- ·	Co	ontinue to				

量子論電子工学(2)

The shift of the electronic level in the magnetic field or Zeeman splitting will be explained by calculation by the perturbation method. Abnormal Zeeman effect when the magnetic field is weak, normal Zeeman effect, Paschen back effect in case of strong, handling of spin orbit interaction will be discussed.

Hartree-Fock equation (2 times)

We describe the calculation of electronic levels of multi-electron atoms about the Hartley method, the Hartley-Fock method, and the Hartree-Fock-Slater method by mean field self-consistent method.

Molecular model (2 times)

In the case of bimolecular molecules, we will explain the valence bonding method and the molecular orbital method, and explain the hydrogen level, the electronic level of hydrogen molecule, that is, the binding energy and the bonding distance. Also, we will talk about the type of molecular bond and hybrid trajectory.

Crystal field and magnetism (2 times)

The electron orbit of the atom in the crystal will be explained from the crystal electric field. In addition, we introduce Heisenberg's effective Hamiltonian and outline the paramagnetism and electronic correlation of the substance.

[Class requirement]

Basics of quantum mechanics (Schrodinger equation, one dimensional potential problem, concept of expectation, etc.)

[Method, Point of view, and Attainment levels of Evaluation]

Examination and report

[Textbook]

Instructed during class

[Reference books, etc.]

(Reference books)

Introduced during class

[Regarding studies out of class (preparation and review)]

Please do exercises voluntarily

(Others (office hour, etc.))

Numbering	g coo	de									
		尊体ナノスピ iiconductor N				dep	liated artment title,Na	' D.		ol of Engineering RAISHI MASASHI	
Target year Number of credits 2									se offered period	2019/Second semester	
Day/perio	Day/period Tue.2 Class style Lecture Language Japanese and English										
[Outline a	Outline and Purpose of the Course]										

Spintronics is now attracting tremendous attention, and is recognized as one of the most potential candidates to overcome the limit of the Moore's law. Spintronics possesses attractive and profound basis physics and also a potential to practical applications towards MRAMs and spin FETs. In this lecture, I introduce some important and basic theories and experimental techniques in spintronics using semiconductors, metals, insulators, oxides and so on.

[Course Goals]

Understanding basic physics of spin transport, spin current and spin-orbit coupling. Mastering calculation skills related with these topics.

[Course Schedule and Contents]

Introduction,1time,Spin is a quantum quantity, and thus it is to induced by rotation of an electron (an electron is an elementary particle, i.e., it has no domain. Thus, rotation of an electron cannot be defined). Nevertheless, the spin degree of freedom can be coupled to spatial rotation because spin is a generator of infinitesimal rotation. I explain the essence of spin, its SU(2) algebra and so on.

Relativistic quantum physics and spin-orbit interaction,5times,To understand spin manipulation and spin coherence in semiconductor, it is quite important what the spin-orbit interaction (SOI) is. The SOI is a manifestation of a relativistic effect, and the Dirac equation, the equation of motion in relativistic quantum physics, is derived to understand the SOI. Next, the SOI is explicitly derived be expanding the Dirac equation. As a related important topic, electron motion in graphene, which can be described as massless Dirac fermion, and the Berry phase (a geometric phase that plays an important role in spintronics) of electrons in graphene are discussed.

Electrical and dynamical spin injection into condensed matters and generation of pure spin current ,5-6times, Pure spin current is a quite significant physical current in spintronics using semiconductors and so on. Pure spin current is a current of only a spin degree of freedom without a net charge flow. I introduced some important papers and show how to derive essential equations describing generation and propagation of pure spin current. (1) Spin drift-diffusion equation, (2) Hanle-type spin precession, (3) spin pumping using magnetization dynamics, and (4) spin current circuit theory are discussed.

Recent topics in spintronics,2-3times,Topological insulators and the Berry phase are important topics in modern spintronics. To understand the essence of them, I show the derivation of the Kubo formula, and the calculation of the Hall conductivity based on the Kubo theory. The above mentioned topics are the main contents of this lecture, but I may add or omit some topics as requests from students.

半導体ナノスピントロニクス**(2)**

[Class requirement]

Solid State Physics and Quantum Physics at the level of undergraduate school.

[Method, Point of view, and Attainment levels of Evaluation]

Report submission

[Textbook]

None

[Reference books, etc.]

(Reference books)

For foreign students, I recommend the following review articles: 1. Spin Hall effect, J. Sinova et al., Rev. Mod. Phys. 87, 1213 (2015). 2. Spintronics: Fundamentals and applications, I. Zutic et al., Rev. Mod. Phys. 76, 1 (2004). 3. Nonlocal magnetization dynamics in ferromagnetic heterostructures, Y. Tserkovnyak et al., Rev. Mod. Phys. 77, 1375 (2005).

[Regarding studies out of class (preparation and review)]

(Others (office hour, etc.))

											未更新		
Numbering c	ode												
Course title <english> C</english>			Beam	Apparatus		dep	iliated partment p title,Na				ol of Engineering ssor,GOTOU YASUHITC		
Target year			_	Number	of cred	its	2			e offered eriod	2019/Second semester		
Day/period	Wed	.4	Cla	ss style	Lecture	e				Language	Japanese		
[Outline and	Pur	pose of t	he C	ourse]									
transport of io	n bear ion b	ms, and io eam appli	n-soli cation	d interactio	n will be onship be	e pro etwe	esented en the	. Tal incic	king dent	ion implan ion energy	evaluation of ion beams tation as one of the and implantation depth		
[Course Goals]													
To understand the details of an ion beam apparatus: generation, transport and evaluation of an ion beam. Understanding of the entire ion beam apparatus as a system is also purpose of the class.													
[Course Schedule and Contents]													
[Ion beam systems and their applications] Once Outline of the class is presented. Physical properties of ions in vacuum are given, and ion beam apparatuses and their application will be introduced with some typical examples. [Ion-solid interaction] 3 times Interaction between high energy ion and solid atoms are given. Major topics are: how the ions transfer their energy to the target atoms, i.e., how the ions are decelerated in the solid, and relationship between incident ion energy and implantation depth is given. Concept of sputtering phenomenon is also presented.													
[Nature of ion Concept of the an ion beam is	accel	eration vo	ltage	is introduce	ed to exp	olain	the pri	ncip	ole o	f the ion bea	am systems. Nature of		
	gene are g	eration for iven. Start	vario ting w	us elements with the para	xial ray	equ	ation, c			-	beam extraction and natrix is given. Finally,		
[Mass separators and energy analyzers] 3 times Details of magnetic sector as mass separator are given. Transfer matrix of the mass separator are presented and focusing effect is described. An important parameter of mass resolution is given. Some different kinds of energy analyzers are also introduced. Deflection and detection systems are also introduced.													
[Fundamentals Fundamentals					Several	pun	nps used	d for	ion	beam syste	ms are also introduced.		
[Design of ion Design of an io		•		a given co	ndition	will	be pres	ente					
									C	ontinue to	電子装置特論(2)		

電子装置特論(2)

- - -

[Feedback] Once

In the last class, achievement test will be performed.

[Class requirement]

Vacuum Electronic Engineering (undergraduate course)

[Method, Point of view, and Attainment levels of Evaluation]

Grading will be made with the results of the term-end examination. Achievements of exercises in the class are also taken into consideration.

[Textbook]

Yasuhito Gotoh, Charged Particle Beam Appratus, 2018 version (to be sold at CO-OP shop in Katsura Campus)

[Reference books, etc.]

(Reference books)

Zyunzo Ishikawa ^PCharged Particle Beams (Corona) ISBN:978-4-339-00734-3

[Regarding studies out of class (preparation and review)]

(Others (office hour, etc.))

We will have brief practice in each class. Bring your calculator and A4-size writing papers.

Numbering	code												
Course title <english></english>		報科学 n Informa	tion S	Science		dep	iliated partment p title,Na	-	Prof Grad	essor,TAK duate Scho	ol of Engineering EUCHI SHIGEKI ol of Engineering essor,OKAMOTO RYOU		
Target ye	ar			Number	of cred	its	2		ourse ar/pe	offered riod	2019/First semester		
Day/perio	d Mon.	3	Cla	ss style	Lecture	e				Language	Japanese and English		
[Outline a	nd Purp	oose of t	he C	ourse]									
	e duality	•				<u> </u>			-		he basic picture of nunication, quantum		
[Course G	oals]												
To understand the basic concepts/mechanisms of quantum key distribution, quantum computers, and quantum metrology so that one can read and understand the scientific papers of the related area.													
[Course Schedule and Contents]													
[Class req	uireme	ntl											
Basic unders		-	m me	chanics wil	ll be help	oful.							
[Method, F	Point of	view, a	nd At	ttainment	levels	of E	valuat	ion]				
The number	of days	one has at	tende	ed, and the s	score of	repo	orts will	be c	consi	dered.			
[Textbook]												
No text book	will be	used.											
							· – –		- <u>C</u> o	ntinue to			

量子情報科学**(2)**

[Reference books, etc.]

(Reference books)

Nielsen & Chuang, Quantum Computation and Quantum Information, Cambridge University Press

Shigeki Takeuchi, Quantum Computer, Kodansha (in Japanese)

[Regarding studies out of class (preparation and review)]

The reports are mandatory.

(Others (office hour, etc.))

We welcome your positive questions and comments. We select the language (Japanese or English) used in the lectureb taking into account the situation and hope of the students taking this lecture.

	未更新 Aumboring code												
Numbering	g cod	e											
Course title <english></english>		体工学特論 iconductor Er	ngine	ering, Adv.		dej	iiliated partment b title,Na				ol of Engineering OTO TSUNENOBU		
Target ye	ar			Number	of cred	its	2			e offered eriod	2019/First semester		
Day/perio	od W	'ed.3	Cla	ss style	Lecture	e				Language	Japanese		
[Outline a	nd P	urpose of t	he C	ourse]									
	-	ores the funda onductor mat				or pł	iysics ar	nd ei	ngin	eering, whi	ch are esseantial to		
[Course Goals]													
[Course Schedule and Contents]													
the Boltzma High-field e few phenom Defects in se point defects MOS physic structure are	Band theory,2-3times,Electronic band structures are discussed. Nearly free electron and tight-binding approachs are explained. Band structures of major semiconductors such as Si and GaAs are also discussed. Carrier transport and scattering,3-4times,Carrier transport and electrical conduction are explained by using the Boltzmann transport equation. Scattering mechanism of carriers and mobility are discussed. High-field effect,2-3times,Drift of carriers and junction breakdown under high electric field are discussed. A few phenomena under high magnetic field are also explained. Defects in semiconductors,1-2times,Crystallographic and electronic properties of defects (both extended and point defects) in a semiconductor are explained. MOS physics,2-3times,Energy band diagrams and carrier statistics in a metal/insulator/semiconductor (MIS) structure are discussed.												
[Method, I	Point	t of view, ar	nd Af	tainment	levels	of E	Evaluat	ion]				
Final examin	nation	n and a few re	ports										
[Textbook	c]												
No textbook	t is ass	signed.											
[Referenc	e boo	oks, etc.]											
(Referen S. M. Sze Pl Semiconduc	hysics	s of Semicono	ductor	r Devices (V	Wiley In	ters	cience)	\ P.Y	Y.Yu	and M. Ca	urdona Fundamentals of		
[Regardin	g stu	udies out of	clas	ss (prepar	ation a	nd	review)]					
(Others (office	e hour, etc.))										
*Please visit	t KUL	LASIS to find	louta	about office	hours.								

Numbering	g code	•											
Course title <english></english>	English> Electronic Materials, Adv. department, Job title,Name Professor,KIMOTO TSUNENOBU												
Target ye	ar			Number	of cred	its	2			e offered eriod	2019/Second semester		
Day/perio	d Th	u.2	Cla	ss style	Lecture	e				Language	Japanese		
[Outline a	nd Pu	irpose of t	he C	ourse]									
Fundamenta	ls and	recent prog	ress ir	1 semicondu	uctor ma	teri	als and	vari	ous a	advanced d	evices are explained.		
[Course G	ioals]												
	[Course Schedule and Contents]												
[Course Schedule and Contents] Si semiconductor.3-4times.Bulk growth, wafering, defect engineering, and impurity gettering of Si are													
reviewed. Si Advanced C CMOS devid High-freque are explaine Power devic	[Course Schedule and Contents] Si semiconductor,3-4times,Bulk growth, wafering, defect engineering, and impurity gettering of Si are reviewed. Silicon-On-Insulator (SOI) is also explained. Advanced CMOS devices and materials,2-3times,Basic structures and performance enhancement of advanced CMOS devices, the core devices in LSI, are explained. High-frequency devices and materials,2-3times,Structure and operation principle of high-frequency devices are explained. Semiconductor materials suitable for high-frequency applications are discussed. Power devices and materials,2-3times,Structure and operation principle of power devices are explained. Semiconductor materials suitable for high-frequency applications are discussed.												
[Class red	luiren	nent]											
Basics of so	lid stat	te physics ar	nd sen	niconductor	enginee	ering	2						
[Method, I	Point	of view, a	nd At	tainment	levels	of E	Evaluat	tion]				
Report evalu	ation,	taking acco	unt of	f lecture atte	endance				_				
[Textbook	[]												
No textbook	is ass	inged.											
[Referenc	e boo	ks, etc.]											
(Referei	nce bo	ooks)											
[Regardin	g stu	dies out of	clas	ss (prepara	ation a	nd	review)]					
(Others (office	hour, etc.))										

Numbering	g cod	de	G-EN	G11 5	C816 LB72											
Course title <english></english>			レクトロ ar Electro		ス		de	filiated partment b title,Na		Pro Gra Ass Par	duate Scho fessor, YAM duate Scho ociate Profe t-time Lectu t-time Lectu	IAD ol of essor, urer,I	A HI Engi KOE	ROF ineer 3AY A KI	FUM ing ASH EI	II KEI
Target ye	ar				Number	of cred	lits	2			e offered eriod	201	9/Fii	rst se	emes	ster
Day/perio	d N	/Ion.	5	Cla	ss style	Lecture	e				Language	Japa	anese	è		
[Outline a 近年、有機 みつつある 輸送性につ 気特性を学	ELラ 。本 いて	 ディ に 講事	スプレイ _長 では、 その微視	や有 や の か 般 的 機 構	 幾トランジ りに電気伝 構の基礎を	導性が 理解す	著し ると	っく低い とともに	と 、 1	考え 有機	られている 分子の有す	ら有様	幾分子 さます	子の [:] ざま:	キャ な光	リア ・電
[Course G 有機分子-電 の基礎を理 関係を学習	『極り 解す	<u>-</u> 界面 「るく	とともに	、個く	マの分子が											
[Course S					-											
分子エレク 分子エレク うとすっつ の てい 展 て の る に	トロ 子ス 分野 。] 二 / くケ - 予 了 不 下	フスは、 - ルエレ ら構成さ オ料とし	単一ヶ クトロ れる。 ての有	子あるい コニクスと 両者は異	、主に なる視	有機 点力	機薄膜系 からの研	を 究:	対象 分野	とする有様 であるが、	と、 して して して して して して して して して して して して して	莫工し 寺に引	レク 歯く ²	トロ 相互	Iニク [に関
分子 / 有機 分子エレク などの基本	トロ	ニ	フス研究	におい	て用いら	れるさ										
有機薄膜の 有機薄膜の 分子の電気	作製	と方法	まや結晶	化挙重	前について		-		•			≚導体	本性的	分子、	、誘	電性
有機半導体 電界発光(料において 研究動向に	EL) 、そ) デ の=	ィスプレ キャリア	イヤ 伝導機	有機太陽電											
分子エレク 今後の分子						て説明	する	3.								
		-				·				Co	ntinue to 分子	エレ	クトロ	ニクジ	ス (2)

分子エレクトロニクス (2)

- -

学習到達度の確認(1回) 学習到達度を確認する。

[Class requirement]

電子物性,固体物理に関する基礎知識があればよい。

[Method, Point of view, and Attainment levels of Evaluation]

4回程度のレポートにより評価する。

[Textbook]

ノート講義スタイルとする.また適宜資料を配布する.

[Reference books, etc.]

(Reference books)

Introduced during class

[Regarding studies out of class (preparation and review)]

配布資料ならびにノートを整理し、各自で講義内容を復習すること。

(Others (office hour, etc.))

当該年度の授業回数に応じて一部を省略することがある。 また授業順序についても適宜変更するこ とがある。 隔年開講科目。

Numbering c	ode												
Course title 表 <english> Su</english>	面電子物性」 Irface Electron		perties		dej	iliated partment b title,Na		Profe Gradu	essor,YAM uate Schoo	ol of Engineering IADA HIROFUMI ol of Engineering ssor,KOBAYASHI KEI			
Target year			Number	of cred	its	2		ourse o ar/per	offered riod	2019/First semester			
Day/period	Tue.5	Cla	ss style	Lecture	e			L	anguage	Japanese and English			
[Outline and	Purpose of	the C	ourse]										
12													
[Course Goa	aisj												
	[Course Schedule and Contents]												
[Course Sch	edule and C	onter	its]										
,2times,			_										
,3times,													
,4times,													
,2times,													
,3times,													
,1time,													
[Class requi	rement]												
None													
[Method, Po	int of view a	and A	tainment	levels	of F	valuat	ion	1					
Linearioa, r o						- Vuluu							
[Toythook]					_		_						
[Textbook]													
[Reference l	books, etc.]												
(Reference	e books)												
[Regarding	studies out o	of clas	s (prepara	ation a	nd	review)]						
(Others (of	ice hour, etc	:.))											
*Please visit K	ULASIS to fir	d out a	about office	hours.									

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Numbering	j cod	e											
]性工学 cal Properties	and	Engineerinş	5	depa	liated partment title,Na	, me	Prof Grad	fessor,KAW duate Schoo	ol of Engineerin VAKAMI YOU ol of Engineerin sor,FUNATO M	JICHI ng	
Target yea	ar			Number	of credi	its	2	C οι	urse	e offered eriod	2019/First ser		
Day/perio	d Tו	ue.4	Cla	iss style	Lecture	>				Language	Japanese		
[Outline ar	nd P	urpose of t	he C	ourse]									
		_											
[Course Goals]													
[Course Schodule and Contents]													
[Course Se	[Course Schedule and Contents]												
[Course Schedule and Contents] 2-3 Itimes, 7-8 Itimes, 4-5 Itimes, 1 Itimes,													
[Class req	uire	ment]											
None													
[Method, F	oint	t of view, ar	nd Af	tainment	levels c	of E	valuat	ion]					
[Textbook]	.]												
[Reference	e bo	oks, etc.]											
(Referen	ice b	ooks)											
[Regarding	g stı	udies out of	clas	ss (prepar	ation ar	nd r	eview)]					
(Others (c	offic	e hour, etc.))										
*Please visit	KUI	LASIS to find	l out a	about office	hours.								

Numbering	g cod	e									
		子デバイス atum Optoele	ics Devices		department,			Graduate School of Engineering Professor,NODA SUSUMU Graduate School of Engineering Associate Professor,ASANO TAKASHI			
Target year Number				Number	of cred	lits 2 Cours				offered riod	2019/Second semester
Day/perio	d Tu	ıe.4	Cla	ss style	Lecture			L	_anguage	Japanese	
[Outline a	[Outline and Purpose of the Course]										

This course first explains electron system control and optic interactions via different kinds of quantum structure. To do so, the density matrix is derived, and the optical-absorption coefficient is determined using transmission matrix elements within quantum wells, quantum dots, and density of state. Next, it is shown that control is not only possible for electron systems but also for photon systems. Finally, several examples of photonic devices are introduced and explained.

[Course Goals]

Students will become adept at methods of calculating the light absorption coefficient and the refractive index within quantum structures. Students will also gain an understanding of the interaction of light (photons) and electrons.

[Course Schedule and Contents]

1. Introduction (1 class)

The academic background of photonic device engineering is described.

2. Analysis methods for electron/photon interactions (7 classes)

After a review of the basics of quantum mechanics, discussion is made of two-level system and light interaction. The necessity of density matrix theory is introduced, and it is shown that this can be used to describe both a pure state and a mixed state.

Explanation is made of the differences between energy relaxation and pure phase relaxation by deriving those differences from a physics (physical) model. Further, the steady state response of the density matrix vis-#224-vis light is derived, and explanation is made of methods of using this to calculate changes in the complex dielectric constant, the absorption coefficient, and the refractive index.

3. Electron system control and electron/photon interactions (4 classes)

Explanation is made of the interactions of electrons and light within various kinds of quantum structures. Taken up first are quantum wells, with discussion of a calculation method, using integration with consideration of band structure and state density, of the complex dielectric constant. After showing the absorption spectra and polarization characteristics of intersubband transitions, explanation is made of absorption spectra and polarization characteristics in interband transitions.

4. Photon control and electron/photon interactions (2 classes)

Discussion is made of spontaneous emission control based on photon state control. Taken up as examples of photon system control methods are optical microresonators and photonic crystals, and advanced control of light/electron interactions are introduced.

5. Confirmation of extent of student learning (1 class) Confirmation is made of the extent of student learning.

Continue to 光量子デバイス工学(2)

光量子デバイス工学**(2)**

[Class requirement]

None

[Method, Point of view, and Attainment levels of Evaluation]

Evaluations are made on the basis of reports.

[Textbook]

The lecture notes format is used in this course.

Other reference materials may be distributed and discussed as necessary.

[Reference books, etc.]

(Reference books)

Murray Sargent III, Marlan O. Scully, Willis E. Lamb, Jr. ^PLaser Physics (Westview Press) ISBN: 9780201069037

[Regarding studies out of class (preparation and review)]

Nothing of note.

(Others (office hour, etc.))

Numbering	code										
	量子計測工学 Quantum measurement Affiliated department, Job title,Name Graduate School of Engineering Associate Professor,SUGIYAMA KAZU										
Target yea	r			Number	of cred	lits	2		urse offered ar/period	2019/Second semester	
Day/period	Mon.	4	Cla	ss style	Lecture	e			Language	Japanese and English	
[Outline and	[Outline and Purpose of the Course]										
As an example of high precision measurements using quantum phenomena, frequency standards, which is realized with the smallest uncertainty in all measurement quantities at present, are discussed. The principle and evaluation of frequency standards are explained.											
[Course Go	als]										
-	The goal of this lecture is to understand that precision measurements are realized with combination of the best technologies and is based on physics.										
[Course Sc	hedul	e and Co	onten	its]							
postulate and of Fundamentals spectroscopy a Cesium freque interpretation Specification of evaluation of the Noise,2times,1 Relativistic the Others,1time,1 Evaluation of [Class requ Fundamentals	[Course Schedule and Contents] Introduction and principle of time measurement, 1time, Two principles of time measurement: Reproducibility postulate and dynamic model Fundamentals of atomic frequency standards,2.5times, Atomic states, its energy shifts, high-resolution spectroscopy and high-sensitive detection Cesium frequency standard and atom interferometer,2.5times, Principle of Ramsey resonance and its interpretation as atom interferometer Specification of frequency standards: evaluation methods and theoretical limit,2times,Fundamentals of evaluation of frequency stability with Allan variance, and theoretical limit of frequency stability Noise,2times,Incoherent signals and shot noise Relativistic theory and time,3times,Impact of special and general relativistic theory on time measurement Others, 1time,If we have time, the frequency noises of masers and lasers, and other subjects will be lectured. Evaluation of understanding,1time, Fundamentals of physics (quantum physics, in particular) and electric circuits including linear system. The level which average graduate students of electric and electronic science and technology acquire is sufficient										
[Method, Po	oint of	[;] view, aı	nd At	tainment	levels	of E	valuat	ion]		
Report(two tir	nes, at	the first le	ecture	and the aft	er all leo	cture	es)		-		
[Textbook]											
Some material	Some materials will be provided in the case we need.										
[Reference	books	s, etc.]									
	[Reference books, etc.] (Reference books) C. Audoin and B. Guinot 『The Measurement of Time』 (Cambridge University Press) ISBN:0521003970 Continue to 量子計測工学(2)										

量子計測工学**(2)**

(This is a nice book for this topic. I recommend anyone who are interested in this topic to buy one.) Masao Kitano ^PBasics of Electronics Circuit (in Japanese) (Reimei) (This is a textbook used on the lectuer "Electronics" in fucity. I will use this on the topic "Noise".)

 $(\, \text{Related URLs} \,)$

(https://www.kogaku.kyoto-u.ac.jp/lecturenotes/(Unfortunately, this web page is discontinued from 2014. New pages would appear on PandA system.))

[Regarding studies out of class (preparation and review)]

In case you need.

(Others (office hour, etc.))

Office of instructor: A1-124

Numbering c	ode										
	気伝導 ectrical Cor	l Matter	dep	iliated partment p title,Na		Associate F Graduate	Profes Scho	ol of Engineering sor,KAKEYA ITSUHIR(ol of Energy Science TOSHIYA			
Target year		of cred	its	2		urse offer ar/period	ed	2019/First semester			
Day/period	riod Wed.2 Class style Lectur							Langu	age	Japanese	
[Outline and Purpose of the Course]											
A fundamental aspect of the electrical conduction in solids is discoursed in terms of physics based on the classical dynamics and later on the quantum physics. An important concept of the phonon and the electron-phonon is discoursed, which play a very important role in the electrical conduction in solids. The electrical conductivity is discoursed with a frequency from 0, that is dc, to optical frequency, by which a unified understanding of electrical conduction and the optical property is intended.											
[Course Goa	[Course Goals]										
This class in intended to bestow the understanding of the solid state physics of a level dealt in the celebrated textbook by Ashcroft and Mermin. It is also intended for those attending in this class to acquire an ability sufficient to strive through such a textbook by himself or herself after the class is completed.											
[Course Schedule and Contents]											
Lattices and reciprocal lattices (2 classes) Explanation is made of lattices and reciprocal lattices, a fundamental item for understanding electron properties within an atom. Fundamentals of quantum mechanics, and the hydrogen atom model (2 classes) A simple review is made of quantum mechanics, and explication is made of electron states (energy, spatial distribution, etc.) within hydrogen and atoms other than hydrogen.											
Free-electron F Explanation is provided of cor	made of the	e free-elect				0			rerall	explanation is	
	ture of elec									tion is provided of	
conductivity and the band structures of conductors, semiconductors, and insulators. Electron-phonon interactions, and conductivity in metals and semiconductors (2 classes) Lattice vibration is explained via quantized phonons (Bose particles) and Bose statistics, and lattice specific heat is introduced via determination of phonon density of state. Phonon scattering and electron scattering are explained. On this basis, explanation is then provided regarding the heat dependent nature of resistivity in metals, as well as of the Bloch-Gr#252neisen law at low temperature. Conductivity in semiconductors, especially scattering, is also explained.											
Superconductiv With respect to Meissner effect	supercond	uctive phe		-				-		quation, of the nd order parameters are	
								Continu			

電気伝導**(2)**

introduced. The relationship between phase and vector potential, important for superconductivity, is explained, as well as the Josephson effect. Explained also is magnetic flux quantization within type II (high field) superconductors.

Feedback lesson (1 class)

Confirmation of learned content is made based on evaluations of short tests and the score on the final examination, etc.

[Class requirement]

Those who would like to attend in this class are recommended to study electrodynamics, statistical physics, and introduction to the solid state devices in advance. The lecture is, however, given in Japanese.

[Method, Point of view, and Attainment levels of Evaluation]

Basically, an examination is imposed after the last class. A report may be imposed in case of necessity.

[Textbook]

C. Kittel ^PIntroduction to Solid State Physics 8th ed. (Wiley) ISBN:0471680575

[Reference books, etc.]

(Reference books)

Solid State Physics by Ashcroft and Mermin

[Regarding studies out of class (preparation and review)]

Preparing before classes and reviewing after classes are recommended.

(Others (office hour, etc.))

Numbering	g code											
	ourse title 融合光・電子科学の展望 English> Prospects of Interdisciplinary Photonics and Electroni								Graduate School of Engineering Professor,FUJITA SHIZUO			
Target ye	earNumber of credits2Course offered year/period2019/First s								2019/First semester			
Day/perio	Day/period Fri.2 Class style Lecture Language Japanese and English										Japanese and English	
[Outline and Purpose of the Course]												
[Course G	ioals]											
[Course S	chedul	e and Co	onten	ts]								
[Course Schedule and Contents]												
[Class req	luireme	ent]										
None												
[Method, I	Point o	f view, a	nd At	tainment	levels	of E	Evaluat	ion]			
[Textbook]											
[Referenc	e book	s, etc.]										
(Referei	(Reference books)											
[Regardin	g studi	es out o	f clas	s (prepara	ation a	nd	review)]				
(Others (-									
*Please visit	KULA	SIS to find	l out a	about office	hours.							

Numbering	g code										
	<english> Advanced Seminar in Electronic Science and Engineering I Job title,Name Professor,KIMOTO TSUNENOBU</english>										
Target ye	ar	Number of credits2Course offered year/period2									2019/First semester
Day/perio	Day/periodThu.3,4,Fri.3,4Class stylePractical trainingLanguageJapanese										
[Outline and Purpose of the Course]											
[Course G	oalsj										
[Course S	chedul	e and Co	nter	its]							
,6times,											
[Class req	uireme	nt]									
None											
[Method, F	Point of	i view, ar	d A	tainment	levels o	of Ev	aluat	ion]]		
[Textbook]										
[Reference	e book	s, etc.]									
(Referer	nce boo	oks)									
[Regarding	g studi	es out of	clas	s (prepara	ation a	nd re	view)]			
(Others (office h	our, etc.)))								
*Please visit	KULA	SIS to find	outa	about office	hours.						

Numbering	g cod	de										
Course title <english></english>	sh> Advanced Seminar in Electronic Science and Engineering II Job title,Name Professor,KIMC								ol of Engineering OTO TSUNENOBU			
Target ye	ear		Number of credits2Course offered year/period2019/Fir									2019/First semester
Day/perio	ay/periodThu.3,4,Fri.3,4Class stylePractical trainingLanguageJapanese											
[Outline and Purpose of the Course]												
[Course G	Boals	s]										
[Course S	Sche	dule	and Co	onten	its]							
,6times,												
[Class rec	quire	emen	it]									
None												
[Method,	Poin	t of	view, ar	nd At	ttainment	levels	of E	Valuat	ion]		
[Textbook	(]											
[Referenc	e bo	oks,	etc.]									
(Refere	nce	booł	(S)									
[Regardin	g st	udie	s out of	clas	ss (prepara	ation a	nd	review)]			
(Others (offic	e ho	ur, etc.))								
*Please visi	t KU	LAS	S to find	outa	about office	hours.						

Numbering code G-INF06 53631 LJ72 G-INF06 53631 LJ11											
Course title	dv.	Affiliated department.				Graduate School of Informatics Professor,ONODERA HIDETOSHI					
Target yea	rear1st year students or aboveNumber of credits2Course offered year/period2019/First sem								2019/First semester		
Day/period	We	d.4	Class style	Lecture	e				Japanese		
Class typ	Class type 専攻基礎科目										
- 集積回路はコ る。集積回距 積回路は195 影響を与えて 計工程を中心 具体的には、 MOSデバイご ついて講義で イン のいて講義で イン がを学修する An integrated reduction of a integrated circ the course ince the course ince technology, C and LSI desig	[Outline and Purpose of the Course] 集積回路はエレクトロニクスシステムの高機能化・高信頼性化・低価格化を担うキーデバイスであ る。集積回路製造技術の着実な進歩により、集積可能な回路規模は等比級数的に増大している。集 積回路は1958年の誕生以来、エレクトロニクス分野に革命を起こしただけでなく、社会にも大きな 影響を与えている。本講義では、このような集積回路の設計技術について、特に論理設計以降の設 計工程を中心に講述する。 具体的には、集積回路設計技術の現状と技術動向、CMOSプロセス技術、CMOSレイアウト設計、 MOSデバイス特性、CMOSスタティックゲート、CMOSダイナミックゲート、LSI設計法、FPGAに ついて講義する。本講義は、エレクトロニクスシステムの中核となる集積回路の概要とその設計技 術を学修することを目的とする。										
[Course Goals] 本講義の学修により、集積回路の設計フローを理解し、簡単なディジタル回路に対して論理設計、 回路設計、レイアウト設計が行える程度の知識を修得することができる。 By learning this lecture, you can obtain basic knowledge on a design method of integrated circuits such that you can complete logic, circuit and layout design for a simple digital circuit.											
	まっ	DNて講述	-		状汤	しを見極	ヹめ、	必	要な場合に	こは説明や課題を追加	

1. 集積回路設計技術の現状と技術動向: 最先端の集積回路を例にとり、集積回路の現状を説明する。 集積回路の発展の経過を述べ、技術動向を検討する。 2. CMOSプロセス技術: CMOSを用いた集積回路の製造プロセスについて説明する。各製造工程で、

_____ Continue to 集積回路工学特論(2)

集積回路工学特論(2)

どのようなフォトマスクが必要になるかを述べる。

3. MOSデバイス特性: 微細構造を持つMOSFETの動作特性を説明する。抵抗素子、容量素子の実現 法を示す。微細化により配線性能が低下する問題と、その克服法について述べる。

4. CMOSスタティックゲート・ダイナミックゲート: 論理ゲートの回路構造として、CMOS相補型ス タティックゲートとダイナミックゲートを取り上げ、動作原理や動作特性について説明する。更に、 動作特性の解析法や設計法を示す。

5. LSI設計法:大規模な集積回路の設計法として、同期式設計について説明する。同期式設計におけ るタイミング設計技術やクロッキング技術を講述する。低消費電力化設計技術について説明する。 6. FPGA: ユーザーの手元でカスタム化が可能なLSIとして、FPGAが利用されるようになってきた。 FPGAの原理や設計法、その応用について説明する。

Following topics will be covered. By assessing the understanding of the students and adding explanations and tasks when necessary, we will spend 2-3 weeks for each topic.

1. Current status and future directions of Integrated Circuit Technology: The current status of integrated circuit development will be explained. Brief history and future directions of integrated circuit technology will be covered.

2. CMOS Process Technology: Fabrication process of CMOS will be explained with particular emphasis on photo-masks required for lithography.

3. MOS Devices: Structure and performance characteristics of MOSFET, capacitor and resister will be explained. Performance degradation of scaled interconnect will be discussed with possible solutions.

4. CMOS Static and Dynamic Gates: CMOS complementally static gates and dynamic gates will be presented with performance analysis and design methods.

5. LSI Design Methodology: Synchronous design method will be explained. Timing analysis and clocking techniques will be discussed. Low power design methodology will be explained.

6. FPGA: Field programmable gate array and its application will be explained.

[Class requirement]

電子回路、ディジタル回路、論理回路に関する基礎知識を有すること。

Basic knowledge on electronic circuits, digital circuits, logic circuits

[Method, Point of view, and Attainment levels of Evaluation]

本講義の到達目標は、集積回路の設計フローを理解し、簡単なディジタル回路に対して論理設計、 回路設計、レイアウト設計が行える程度の知識を修得することである。 到達目標の達成度を、授業期間中に適宜実施するレポート試験によって評価する。 レポート試験は全問を解き全回提出を必須とする。 レポート課題に対する考察内容のレベルや妥当性により評点を決める。

The target of this lecture is to obtain basic knowledge on a design method of integrated circuits such that you can complete logic, circuit and layout design for a simple digital circuit.

The level of achievement will be examined by several reports assigned during lectures. All reports discussing all problems are mandatory.

The grade will be reflected by the level and the validity of the discussions in the reports.

Continue to 集積回路工学特論(3)

集積回路工学特論(3)

[Textbook]

講義資料を適宜配布する

Hand-outs will be provided.

[Reference books, etc.]

(Reference books)

Neil H.E. Weste and David Harris [©]CMOS VLSI Design, 4th Ed.² (Addison-Wesley) Jan M. Rabaey, Anantha Chandrakasan, Borivoje Nikolic [©]Digital Integrated Circuits, 2nd Ed.² (Prentice Hall)

[Regarding studies out of class (preparation and review)]

レポート試験の中には、小規模回路の設計課題が含まれる。特性評価には回路シミュレータ (SPICE)が必要になる。SPICEの入手方法を説明するので、各自で使用環境を整えること。回路シミ ュレータの使い方については、概要のみ授業中に説明する。詳細な利用法は各自で自習すること。

Reports include design and analysis of small circuits. A simulation program (SPICE) is required for performance analysis. Instructions for obtaining SPICE are given and students need to install SPICE by themselves. The usage of the circuit simulator is outlined only in the lecture. Complete usage should be studied by yourself.

(Others (office hour, etc.))